CE640-200
[RED]

Commodity Type and Physical Characteristics	
Material	AlGaInP/GaAs
p-pad Electrode	Au Alloy
n-pad Electrode	Au Alloy
Electrode Pattern	Fig.1
Chip Size	510umx320um
Chip Thickness	260um
Emission Area	Φ200um

Electro-Optical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF=20mA		1.90	2.20	V
Reverse Current	IR	Vr=5V			10	uA
Radiated Power	PO	IF=20mA	0.6	0.8	1.2	mW
Luminous Intensity	IV	IF=20mA	50	70		mcd
Side Emission	-	IF=20mA			0	%
Peak Wavelength	λP	IF=20mA	630	640	650	nm
Spectral Radiation Bandwidth	Δλ	IF=20mA		13		nm
Rise Time	tr	IF=20mA		10		ns
Fall Time	tr	IF=20mA		10		ns

Die shall be mounted on TO=18 gold header without resin coated (Ta=25℃)

RoHS Compliant

Fig.1: Electrode Pattern, Chip Size and Emission Area [Unit:um]